JSR Multi-layer Hardmask Materials

Planarization SOC for Topography Process

300 nm Open Area

100 nm Open Area

Latest SOC

ΔFT=1 nm

Standard SOC

ΔFT=16 nm

Thick SOC for Deep Contact Hole Patterning

1. After Litho
2. After SOG Etch
3. After SOC Etch
4. After SiO2 Etch

Etch Condition
Gas: PFC (SOG), O2 (SOC)

Film Stack

JSR Materials
ArF Resist (170 nm)
SOG (130 nm)
SOC (1100 nm)
SiO2 (1000 nm)
Si sub.